TOSHIBA Diode Silicon Epitaxial Planar Type

# HN1D03FU

### Ultra High Speed Switching Application

Built in anode common and cathode common.

#### Unit 1

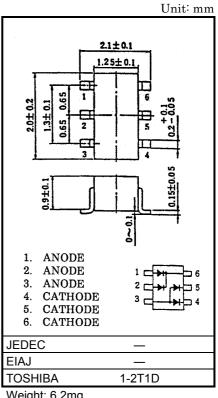
Q1, Q2:  $V_{F(3)} = 0.90V$  (typ.) • Low forward voltage Fast reverse recovery time Q1, Q2:  $t_{rr} = 1.6$ ns (typ.) Small total capacitance Q1, Q2:  $C_T = 0.9pF$  (typ.)

#### Unit 2

 Low forward voltage Q3, Q4:  $V_{F(3)} = 0.92V$  (typ.) • Fast reverse recovery time Q3, Q4: trr = 1.6ns (typ.) Small total capacitance Q3, Q4:  $C_T = 2.2pF$  (typ.)

### Unit 1, Unit 2 Common Maximum Ratings (Ta = 25°C)

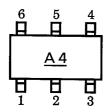
Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	$V_{RM}$	85	V
Reverse voltage	V <sub>R</sub>	80	V
Maximum (peak) forward current	I <sub>FM</sub>	240*	mA
Average forward current	IO	80*	mA
Surge current (10ms)	I <sub>FSM</sub>	1*	Α
Power dissipation	Р	200	mW
Junction temperature	Tj	125	°C
Storage temperature	T <sub>stg</sub>	-55~125	°C

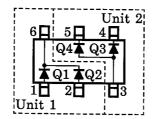


Weight: 6.2mg

#### Marking

# **Pin Assignment (Top View)**



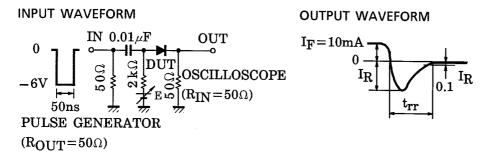


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This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4). In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.

# Fig.1 Reverse Recovery Time (t<sub>rr</sub>) Test Circuit



### Unit 1 Electrical Characteristics (Q1, Q2, Common) (Ta = 25°C)

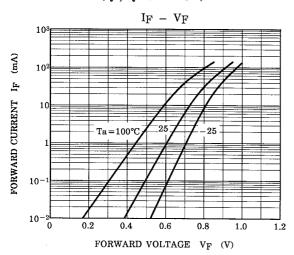
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> = 1mA		0.60	-	V
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA	_	0.72	_	
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA	_	0.90	1.20	
Reverse current	I <sub>R (1)</sub>	_	V <sub>R</sub> = 30V	_	_	0.10	μА
	I <sub>R (2)</sub>	_	V <sub>R</sub> = 80V	_	_	0.50	
Total capacitance	C <sub>T</sub>	_	V <sub>R</sub> = 0, f = 1MHz	_	0.9	3.0	pF
Reverse recovery time	t <sub>rr</sub>	_	I <sub>F</sub> =10mA (fig.1)	_	1.6	4.0	ns

## Unit 2 Electrical Characteristics (Q3, Q4, Common) (Ta = 25°C)

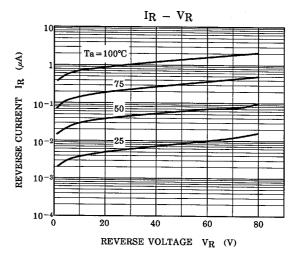
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> = 1mA	1	0.61	_	
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA	_	0.74	_	V
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA	_	0.92	1.20	
Reverse current	I <sub>R (1)</sub>	_	V <sub>R</sub> = 30V	_	_	0.10	μΑ
	I <sub>R (2)</sub>	_	V <sub>R</sub> = 80V	_	_	0.50	
Total capacitance	C <sub>T</sub>	_	V <sub>R</sub> = 0, f = 1MHz	_	2.20	4.0	pF
Reverse recovery time	t <sub>rr</sub>	_	I <sub>F</sub> =10mA (fig.1)	_	1.60	4.0	ns

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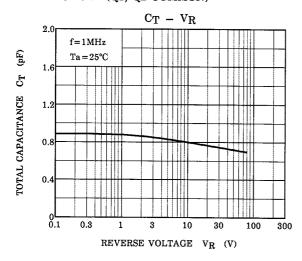
Unit 1 (Q1, Q2 COMMON)



Unit 1 (Q1, Q2 COMMON)

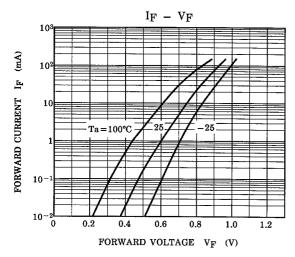


Unit 1 (Q1, Q2 COMMON)

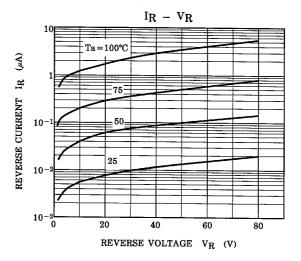


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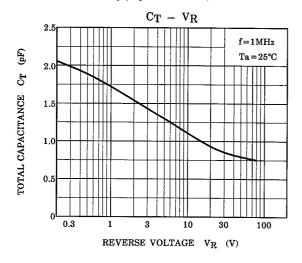
Unit 2 (Q3, Q4 COMMON)



Unit 2 (Q3, Q4 COMMON)



Unit 2 (Q3, Q4 COMMON)



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